



Product Summary

V _{(BR)DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C (Note 7)
60V	250mΩ @ V _{GS} = 10V	1.4A
607	350mΩ @ V _{GS} = 4.5V	1.2A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with a fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Relay And Solenoid Driving
- Motor Control

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

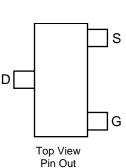
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Charge
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

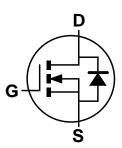
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (03)
- Weight: 0.008 grams (Approximate)



Top View



SOT23



Equivalent Circuit

Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A07FTA	AEC-Q101	7N6	7	8	3,000
ZXMN6A07FQTA	Automotive	7N6	7	8	3,000

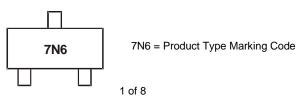
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-Free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

5. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V _{DSS}	60	V
Gate-Source Voltage				V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 10V	$T_A = +70^{\circ}C$ (1	Note 7) Note 7) Note 6)	I _D	1.4 1.1 1.2	А
Pulsed Drain Current (Note 8)				I _{DM}	6.9	A
Continuous Source Current (Body Diode) (Note 7)				Is	1	A
Pulsed Source Current (Body Diode) (Note 8)				I _{SM}	6.9	A

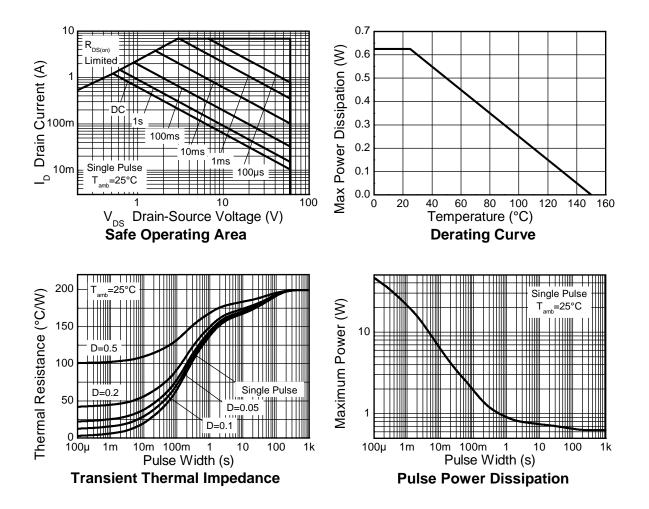
Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 6) Linear Derating Factor		P _D	625 5	mW mW/°C
Power Dissipation (Note 7) Linear Derating Factor		PD	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 6) (Note 7)		R _{0JA}	200 155	°C/W
Thermal Resistance, Junction to Ambient (Note 9)		R _{θJL}	194	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
8. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs - pulse current limited by maximum junction temperate.
9. Thermal resistance from junction to solder-point (at the end of the drain lead). Notes:



Thermal Characteristics (continued)





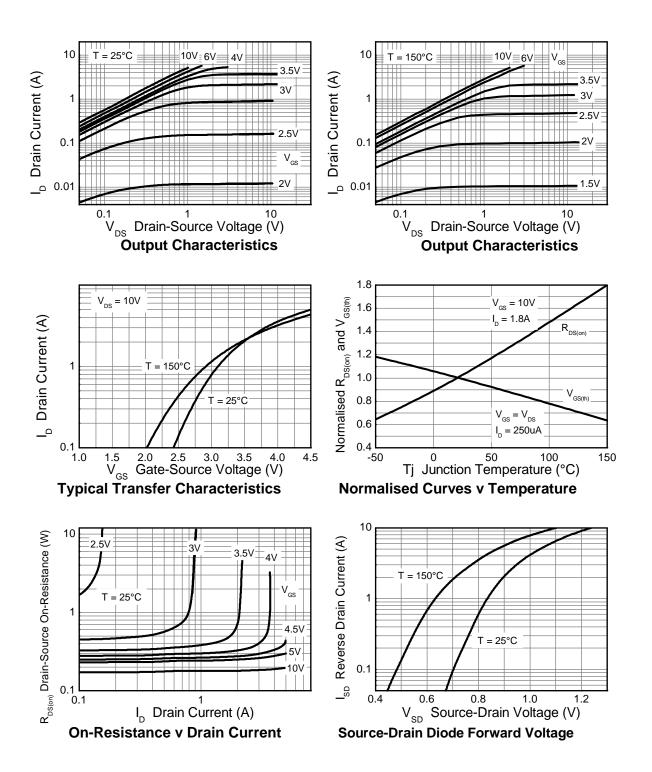
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	—	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	Igss		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0		3.0	V	$I_D = 250\mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 10)	Р			0.250	Ω	$V_{GS} = 10V, I_D = 1.8A$	
Static Drain-Source On-Resistance (Note 10)	R _{DS(ON)}	_		0.350	Ω	$V_{GS} = 4.5V, I_D = 1.3A$	
Forward Transconductance (Notes 10 and 12)	g fs	_	2.3	_	S	V _{DS} = 15V, I _D = 1.8A	
Diode Forward Voltage (Note 10)	V _{SD}		0.8	0.95	V	$T_J = +25^{\circ}C, I_S = 0.45A, V_{GS} = 0V$	
Reverse Recovery Time (Note 12)	t _{rr}	_	20.5	_	ns	T _J = +25°C, I _F = 1.8A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 12)	Q _{rr}	_	21.3	_	nC		
DYNAMIC CHARACTERISTICS (Note 12)	-						
Input Capacitance	C _{iss}	_	166	—		$V_{DD} = 40V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	19.5	_	pF		
Reverse Transfer Capacitance	Crss	_	8.7	_			
Turn-On Delay Time (Note 11)	t _{D(on)}	_	1.8	_		$\label{eq:VDD} \begin{split} V_{DD} &= 30V, \ I_D = 1.8A, \\ R_G &\cong 6.0\Omega, \ V_{GS} = 10V \end{split}$	
Turn-On Rise Time (Note 11)	tr	_	1.4	_			
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	4.9	_	ns		
Turn-Off Fall Time (Note 11)	t _f		2.0	—			
Total Gate Charge (Note 11)	Qg	_	1.65	_	nC	$V_{DS} = 30V, V_{GS} = 5V,$ $I_{D} = 1.8A$	
Total Gate Charge (Note 11)	Qa	_	3.2	—			
Gate-Source Charge (Note 11)	Q _{gs}	_	0.67	_	nC	$V_{DS} = 30V, V_{GS} = 10V,$	
Gate-Drain Charge (Note 11)	Q _{gd}	_	0.82	_	1	I _D = 1.8A	

 Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing. Notes:

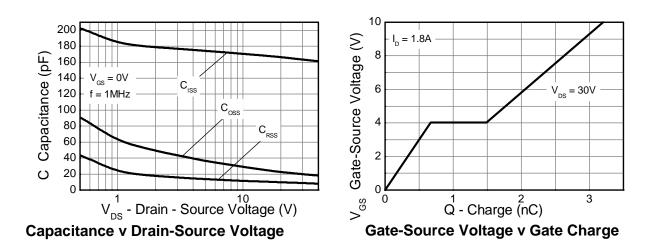


Typical Characteristics

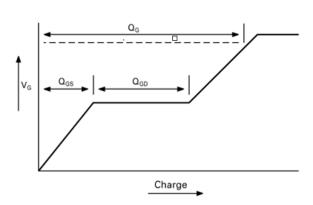




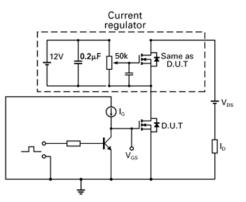
Typical Characteristics (continued)



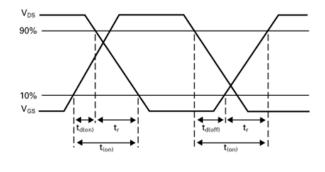
Test Circuits



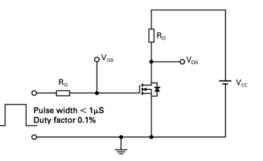
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

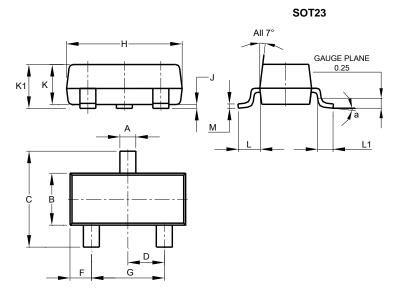


Switching time test circuit



Package Outline Dimensions

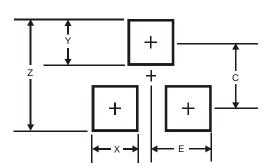
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	a 8°					
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

ZXMN6A07F Document Number DS33547 Rev. 9 - 2 SOT23



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